

**Features:**

- 650V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent

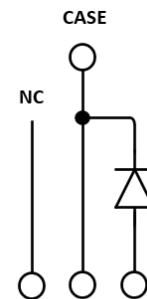
Switching

**Benefits:**

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit
$V_{RRM}$	650	V
$I_F$ ( $T_c = 156^\circ\text{C}$ )	15	A
$Q_C$	34	nC

**Outline**

**TO-247-3**
**Circuit**

**Applications:**

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters

**Maximum Ratings**

Symbol	Parameter	Value	Unit	Test Conditions
$V_R$	DC Peak Reverse Voltage	650	V	$T_J = 25^\circ\text{C}$
$V_{RRM}$	Repetitive Peak Reverse	650	V	$T_J = 25^\circ\text{C}$
$V_{RSM}$	Surge Peak Reverse Voltage	650	V	$T_J = 25^\circ\text{C}$
$I_F$	Continuous Forward Current	53	A	$T_C = 25^\circ\text{C}$
		25		$T_C = 135^\circ\text{C}$
		15		$T_C = 156^\circ\text{C}$
$I_{FRM}$	Repetitive Peak Forward Surge Current	91	A	$T_C = 25^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$
		81		$T_c = 110^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	120	A	$T_C = 25^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$
		109		$T_c = 110^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$
$P_D$	Power Dissipation	227	W	$T_C = 25^\circ\text{C}$
		98		$T_c = 110^\circ\text{C}$
$T_{J,max}$	Operating Junction Temperature	175	$^\circ\text{C}$	
$T_{stg}$	Storage Temperature Range	-55 to 175	$^\circ\text{C}$	

### Thermal characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{thJC}$	Thermal resistance		0.66		$^{\circ}\text{C}/\text{W}$

### Electrical Characteristics

Symbol	Parameter	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
$V_{DC}$	DC Blocking Voltage	650			V	$I_R = 100\mu\text{A}$ , $T_J = 25^{\circ}\text{C}$
$V_F$	Forward Voltage		1.45 1.8	1.7 2.1	V	$I_F = 15\text{A}$ , $T_J = 25^{\circ}\text{C}$ $I_F = 15\text{A}$ , $T_J = 175^{\circ}\text{C}$
$I_R$	Reverse Current		5 10	100 200	$\mu\text{A}$	$V_R = 650\text{V}$ , $T_J = 25^{\circ}\text{C}$ $V_R = 650\text{V}$ , $T_J = 175^{\circ}\text{C}$
$Q_C$	Total Capacitive Charge		34		nC	$I_F = 15\text{A}$ , $dI/dt = 350\text{A}/\mu\text{s}$ $T_J = 25^{\circ}\text{C}$ , $V_R = 400\text{V}$
$C$	Total Capacitance		644 88 85		pF	$V_R = 1\text{V}$ , $T_J = 25^{\circ}\text{C}$ , $f = 1\text{ MHz}$ $V_R = 200\text{V}$ , $T_J = 25^{\circ}\text{C}$ , $f = 1\text{ MHz}$ $V_R = 400\text{V}$ , $T_J = 25^{\circ}\text{C}$ , $f = 1\text{ MHz}$

### Typical Performance

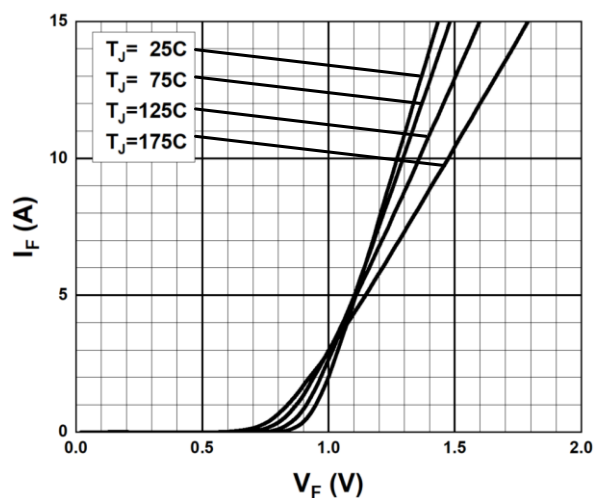


Fig. 1 Forward Characteristics

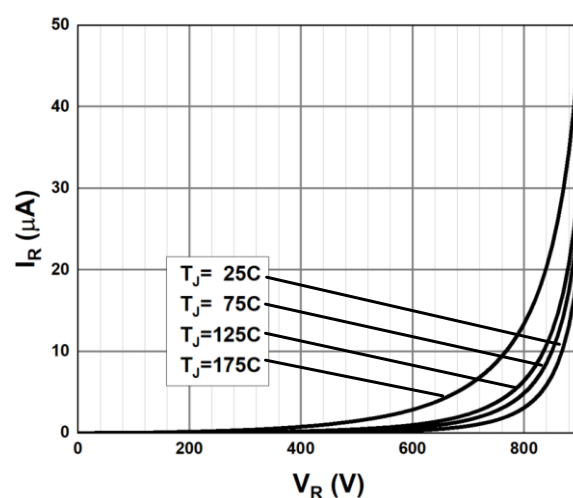
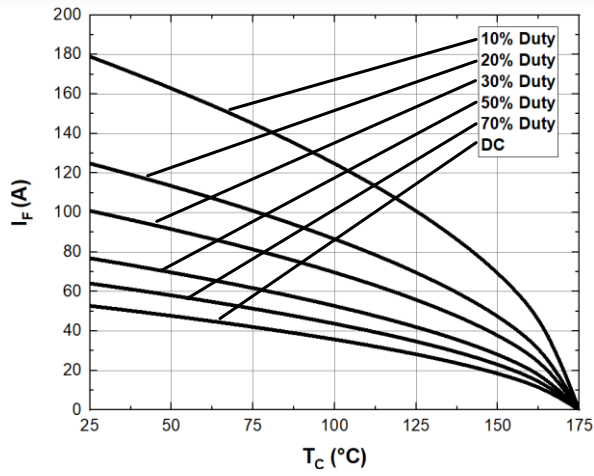
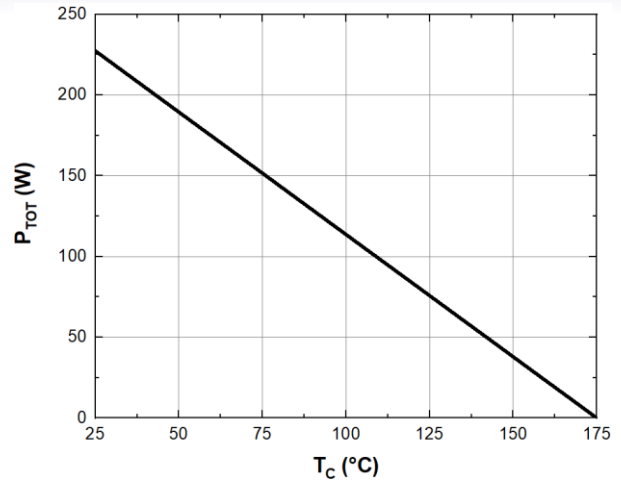


Fig. 2 Reverse Characteristics

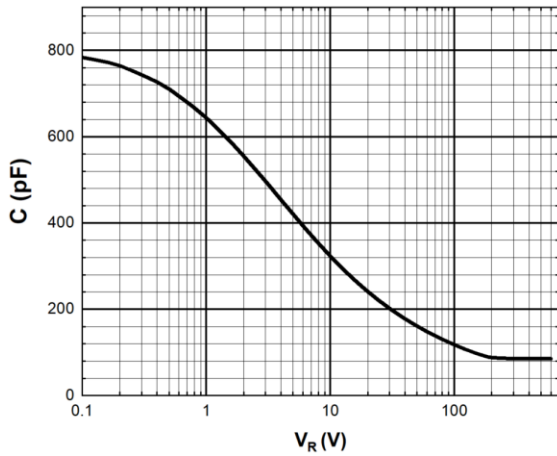
**Typical Performance**



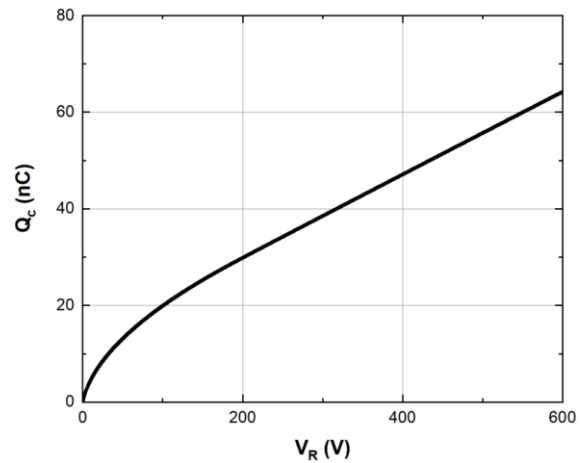
**Fig. 3 Current Derating**



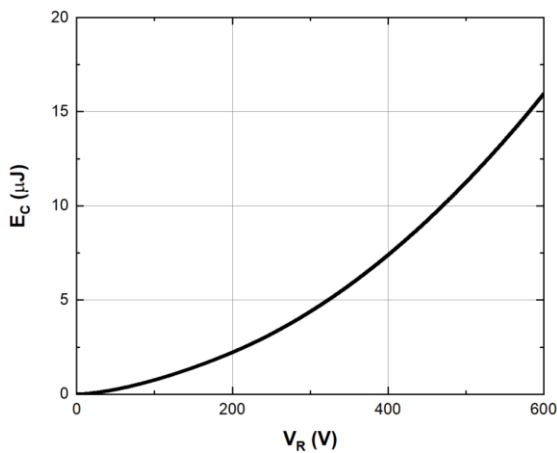
**Fig. 4 Power Derating**



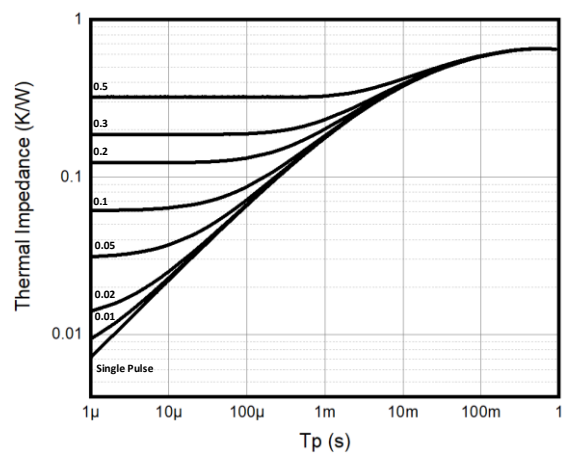
**Fig. 5 Capacitance vs. Reverse Voltage**



**Fig. 6 Recovery Charge vs. Reverse Voltage**



**Fig. 7 Capacitance stored Energy**



**Fig. 8 Thermal Impedance**



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